

STRUCTURE AND METHOD OF MAKING THREE FINGER FOLDED FIELD EFFECT TRANSISTORS HAVING SHARED JUNC- TIONS

Abstract

An integrated circuit including a field effect transistor (FET) is provided in which the gate conductor has an even number of fingers disposed between alternating source and drain regions of a substrate. The fingers are disposed in a pattern over an area of the substrate having a length in a horizontal direction, the area equaling the length multiplied by a width in a vertical direction that is occupied by an odd number of the fingers.